

# BCR5FM-14LJ

700V - 5A - Triac  
Medium Power Use

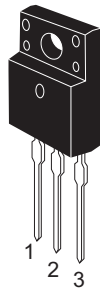
R07DS0961EJ0100  
Rev.1.00  
Nov 19, 2012

## Features

- $I_{T(RMS)}$  :5 A
- $V_{DRM}$  : 800 V ( $T_j = 125^{\circ}C$ )
- $T_j$ : 150°C
- $I_{FGT}$ ,  $I_{RGT}$ ,  $I_{RGT III}$  : 30 mA
- Insulated Type
- Planar Passivation Type
- Viso: 2000 V

## Outline

RENESAS Package code: PRSS0003AG-A  
(Package name: TO-220FP)



1. T<sub>1</sub> Terminal
2. T<sub>2</sub> Terminal
3. Gate Terminal

## Applications

Switching mode power supply, Washing machine, small motor controller, copying machine, electric heater control, and other general controlling devices

## Maximum Ratings

Parameter	Symbol	Voltage class	Unit	Conditions
		14		
Repetitive peak off-state voltage <sup>Note1</sup>	$V_{DRM}$	800	V	$T_j = 125^{\circ}C$
		700	V	$T_j = 150^{\circ}C$
Non-repetitive peak off-state voltage <sup>Note1</sup>	$V_{DSM}$	840	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	$I_{T(RMS)}$	5	A	Commercial frequency, sine full wave 360° conduction, $T_c = 113^{\circ}C$
Surge on-state current	$I_{TSM}$	50	A	60 Hz sinewave 1 full cycle, peak value, non-repetitive
$I^2t$ for fusion	$I^2t$	10.4	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60 Hz, surge on-state current
Peak gate power dissipation	$P_{GM}$	5	W	
Average gate power dissipation	$P_{G(AV)}$	0.5	W	
Peak gate voltage	$V_{GM}$	10	V	
Peak gate current	$I_{GM}$	2	A	
Junction Temperature	$T_j$	-40 to +150	°C	
Storage temperature	$T_{stg}$	-40 to +150	°C	
Mass	—	1.9	g	Typical value
Isolation voltage <sup>Note5</sup>	$V_{iso}$	2000	V	$T_a = 25^{\circ}C$ , AC 1 minute, T <sub>1</sub> • T <sub>2</sub> • G terminal to case

## Electrical Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Repetitive peak off-state current	$I_{DRM}$	—	—	2.0	mA	$T_j = 150^\circ\text{C}$ , $V_{DRM}$ applied
On-state voltage	$V_{TM}$	—	—	1.8	V	$T_c = 25^\circ\text{C}$ , $I_{TM} = 7\text{A}$ , instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	I	$V_{FGTI}$	—	—	1.5	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$V_{RGTI}$	—	—	1.5	
	III	$V_{RGTIII}$	—	—	1.5	
Gate trigger current <sup>Note2</sup>	I	$I_{FGTI}$	—	—	30	$T_j = 25^\circ\text{C}$ , $V_D = 6\text{V}$ , $R_L = 6\ \Omega$ , $R_G = 330\ \Omega$
	II	$I_{RGTI}$	—	—	30	
	III	$I_{RGTIII}$	—	—	30	
Gate non-trigger voltage	$V_{GD}$	0.2/0.1	—	—	V	$T_j = 125^\circ\text{C}/150^\circ\text{C}$ , $V_D = 1/2 V_{DRM}$
Thermal resistance	$R_{th(j-c)}$	—	—	4.9	$^\circ\text{C}/\text{W}$	Junction to case <sup>Note3</sup>
Critical-rate of rise of off-state commutation voltage <sup>Note4</sup>	$(dv/dt)_c$	5	—	—	$\text{V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$
		1	—	—	$\text{V}/\mu\text{s}$	$T_j = 150^\circ\text{C}$

Notes: 1. Gate open.

2. Measurement using the gate trigger characteristics measurement circuit.

3. The contact thermal resistance  $R_{th(c-f)}$  in case of greasing is  $0.5^\circ\text{C}/\text{W}$ .

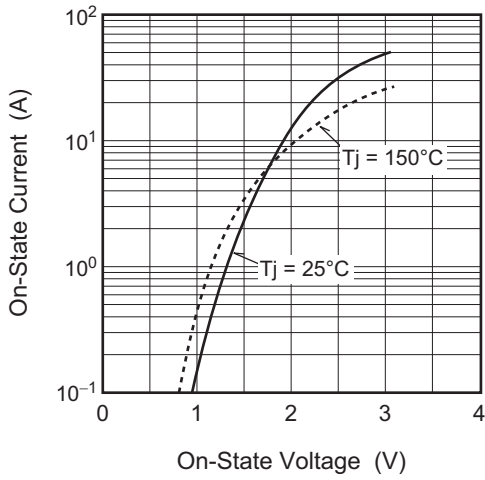
4. Test conditions of the critical-rate of rise of off-state commutation voltage is shown in the table below.

5. Make sure that your finished product containing this device meets your safe isolation requirements.  
For safety, it's advisable that heatsink is electrically floating.

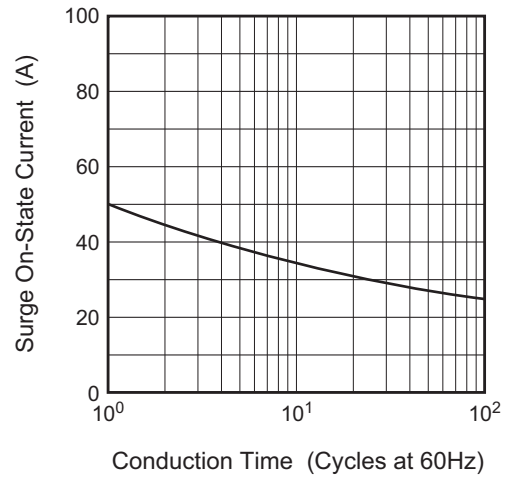
Test conditions	Commutating voltage and current waveforms (inductive load)
1. Junction temperature $T_j = 125^\circ\text{C}/150^\circ\text{C}$ 2. Rate of rise of off-state commutating voltage $(dv/dt)_c = -2.5\text{ A/ms}$ 3. Peak off-state voltage $V_D = 400\text{ V}$	

Performance Curves

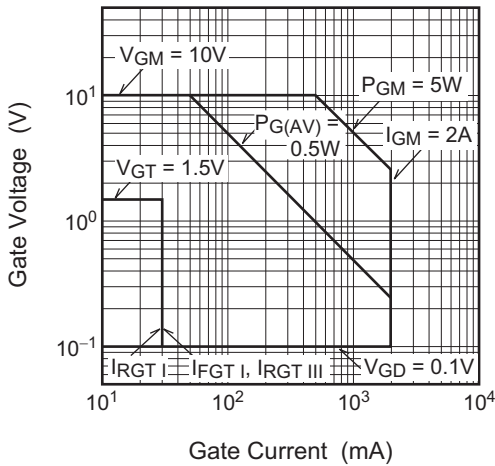
Maximum On-State Characteristics



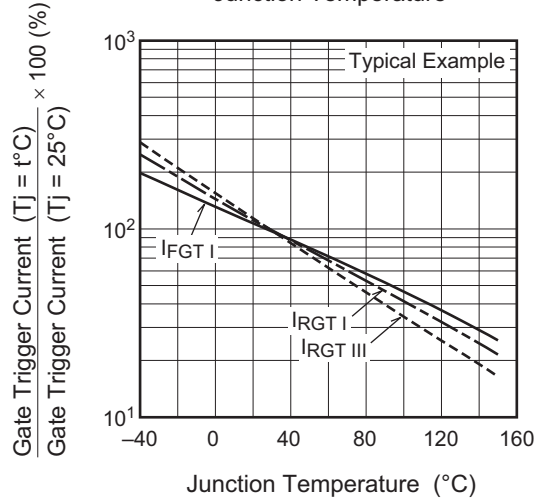
Rated Surge On-State Current



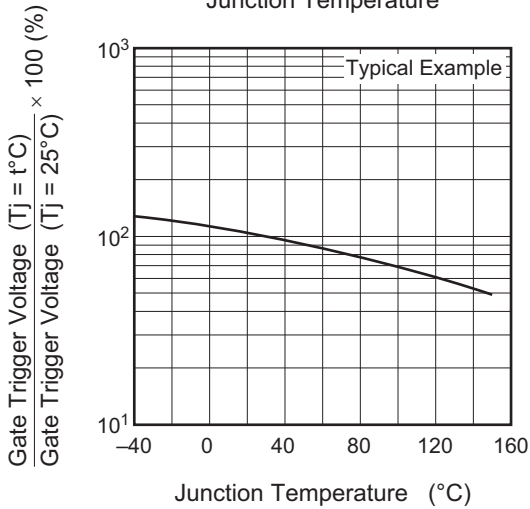
Gate Characteristics (I, II and III)



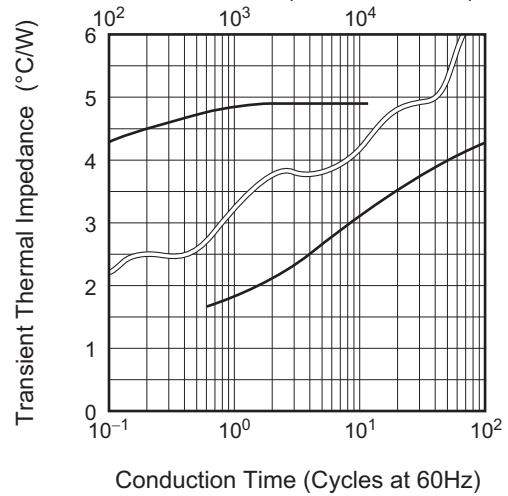
Gate Trigger Current vs. Junction Temperature

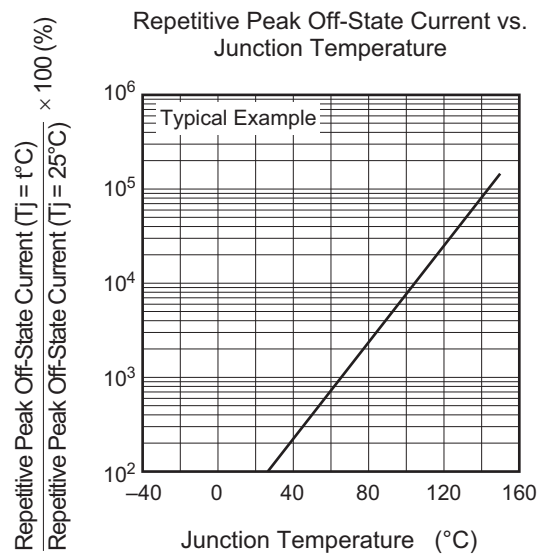
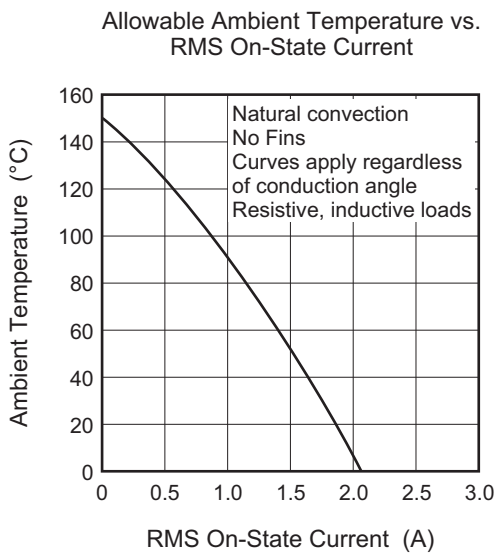
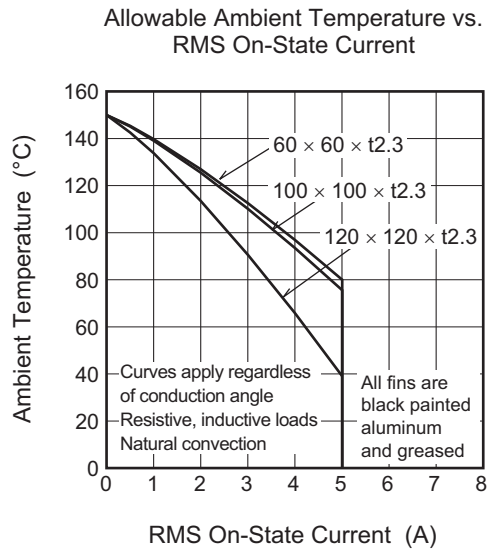
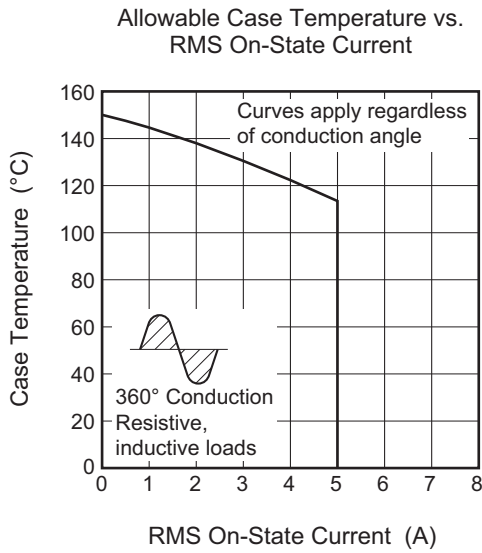
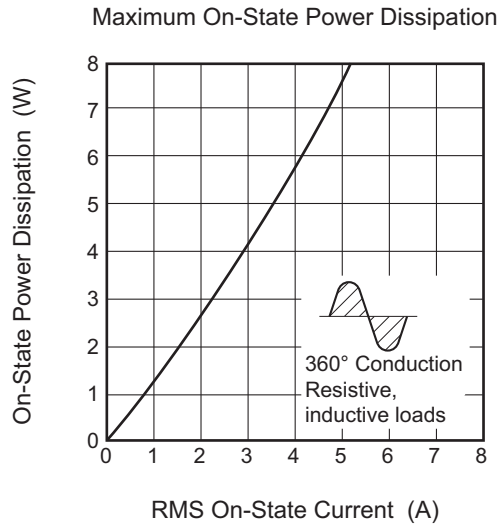
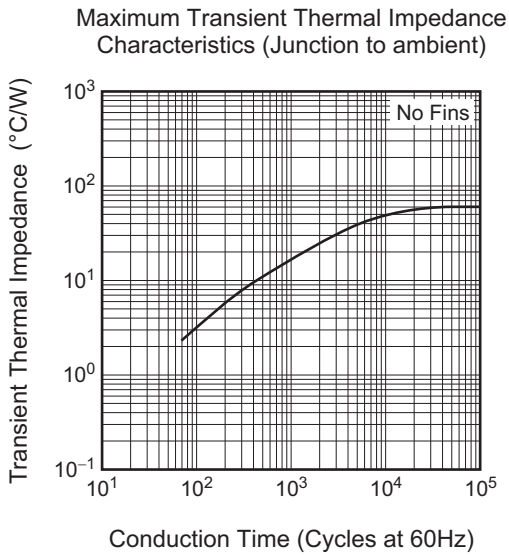


Gate Trigger Voltage vs. Junction Temperature

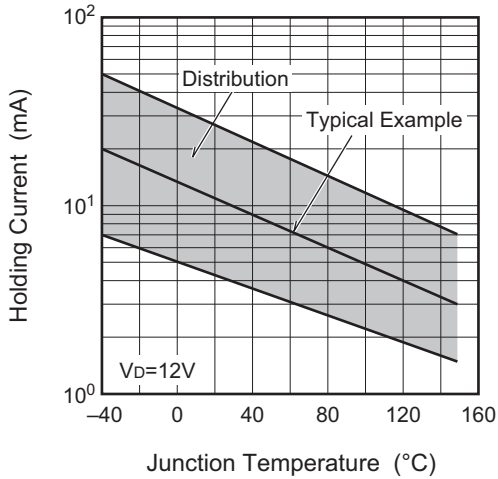


Maximum Transient Thermal Impedance Characteristics (Junction to case)

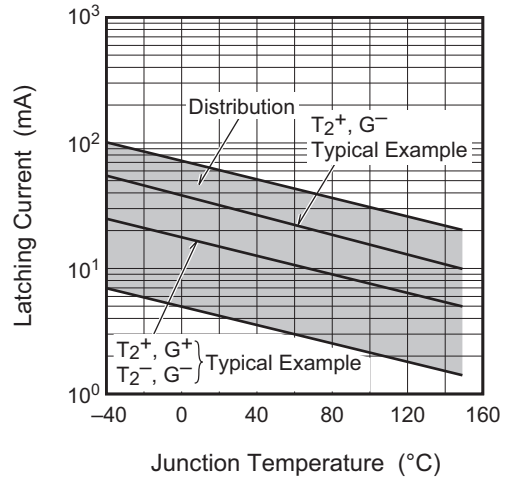




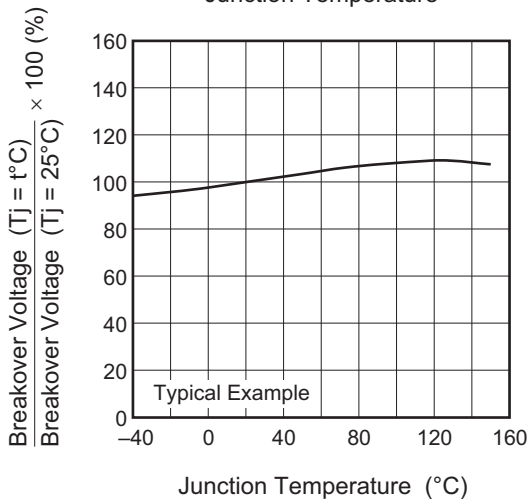
Holding Current vs. Junction Temperature



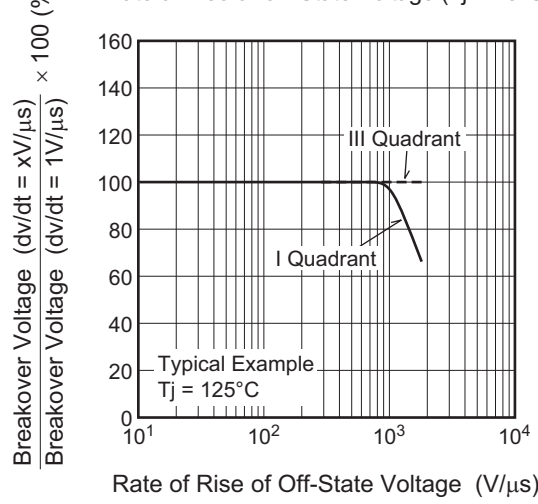
Latching Current vs. Junction Temperature



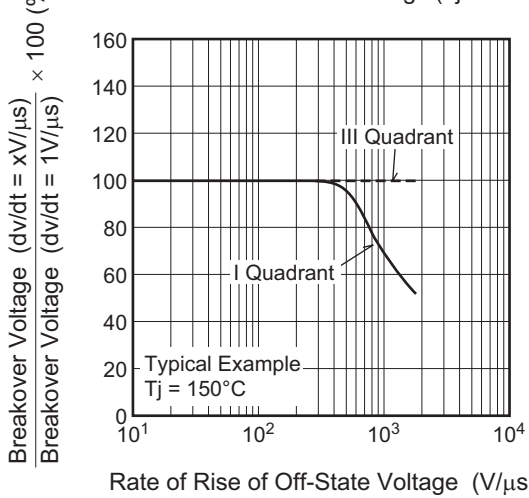
Breakover Voltage vs. Junction Temperature



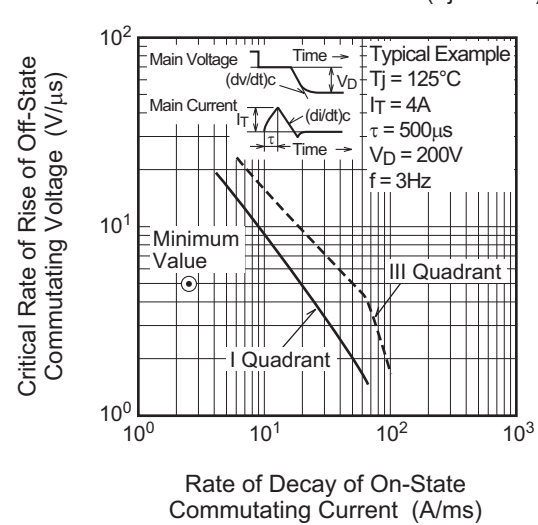
Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=125°C)

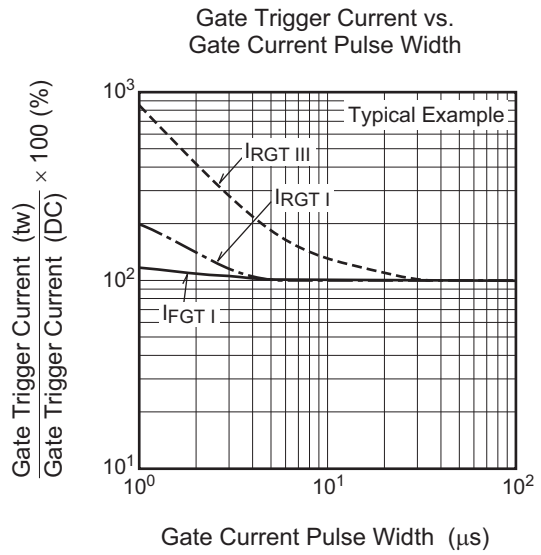
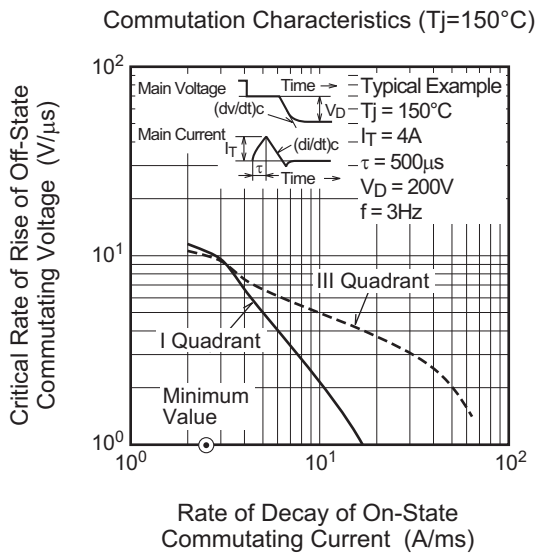


Breakover Voltage vs. Rate of Rise of Off-State Voltage (Tj=150°C)

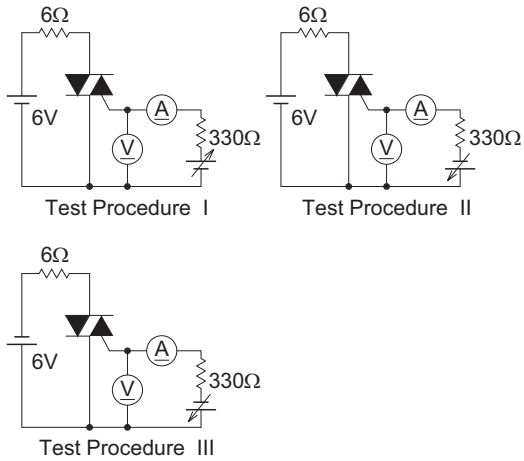


Commutation Characteristics (Tj=125°C)

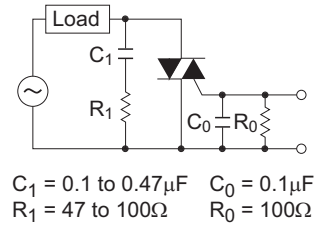




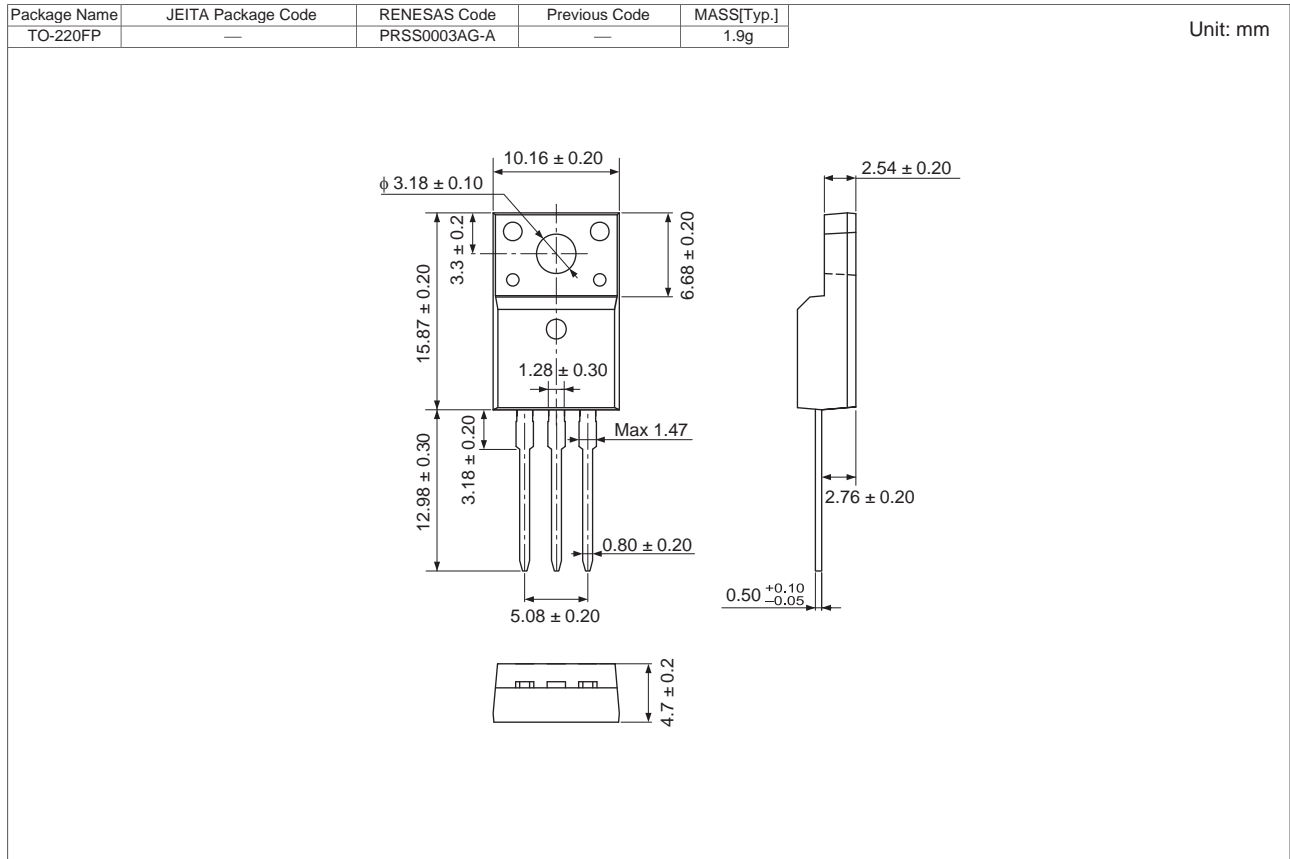
Gate Trigger Characteristics Test Circuits



Recommended Circuit Values Around The Triac



### Package Dimensions



### Ordering Information

Orderable Part Number	Packing	Quantity	Remark
BCR5FM-14LJ#BB0	Tube	50 pcs.	Straight type
BCR5FM-14LJ-A8#BB0	Tube	50 pcs.	A8 Lead form

Note: Please confirm the specification about the shipping in detail.

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2880 Scott Boulevard Santa Clara, CA 95050-2554, U.S.A.  
Tel: +1-408-588-6000, Fax: +1-408-588-6130

**Renesas Electronics Canada Limited**  
1101 Nicholson Road, Newmarket, Ontario L3Y 9C3, Canada  
Tel: +1-905-898-5441, Fax: +1-905-898-3220

**Renesas Electronics Europe Limited**  
Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.  
Tel: +44-1628-651-700, Fax: +44-1628-651-804

**Renesas Electronics Europe GmbH**  
Arcadiastrasse 10, 40472 Düsseldorf, Germany  
Tel: +49-211-65030, Fax: +49-211-6503-1327

**Renesas Electronics (China) Co., Ltd.**  
7th Floor, Quantum Plaza, No.27 ZhiChunLu Haidian District, Beijing 100083, P.R.China  
Tel: +86-10-8235-1155, Fax: +86-10-8235-7679

**Renesas Electronics (Shanghai) Co., Ltd.**  
Unit 204, 205, AZIA Center, No.1233 Lujiazui Ring Rd., Pudong District, Shanghai 200120, China  
Tel: +86-21-5877-1818, Fax: +86-21-6887-7858 / -7898

**Renesas Electronics Hong Kong Limited**  
Unit 1601-1613, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong  
Tel: +852-2886-9318, Fax: +852 2886-9022/9044

**Renesas Electronics Taiwan Co., Ltd.**  
13F, No. 363, Fu Shing North Road, Taipei, Taiwan  
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Tel: +65-6213-0200, Fax: +65-6213-0300

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Tel: +60-3-7955-3390, Fax: +60-3-7955-9510

**Renesas Electronics Korea Co., Ltd.**  
11F., Samik Laved. or Bldg., 720-2 Yeoksam-Dong, Kangnam-Ku, Seoul 135-080, Korea  
Tel: +82-2-558-3737, Fax: +82-2-558-5141